

# EMP109-P1

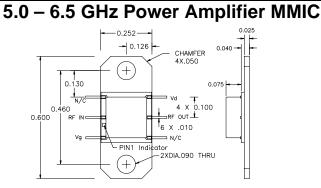
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#### **FEATURES**

- 5.0 6.5 GHz Operating Frequency Range
- 26.5dBm Output Power at 1dB Compression
- 20.0 dB Typical Small Signal Gain
- -40dBc OIMD3 @Each Tone Pout 16.5dBm

#### **APPLICATIONS**

- Point-to-point and point-to-multipoint radio
- Military Radar Systems



Optional Packaging solutions are available contact the Excelics sales team for details.

Caution! ESD sensitive device.

### ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25 °C, 50 ohm, VDD=7V, IDQ=400mA)

SYMBOL	PARAMETER/TEST CONDITIONS	MIN	TYP	MAX	UNITS
F	Operating Frequency Range	5.0		6.5	GHz
P1dB	Output Power at 1dB Gain Compression	25.0	26.5		dBm
Gss	Small Signal Gain	17.0	20.0		dB
OIMD3	Output 3 <sup>rd</sup> Order Intermodulation Distortion @∆f=10MHz, Each Tone Pout 16.5dBm		-40		dBc
Input RL	Input Return Loss		-12		dB
Output RL	Output Return Loss		-6		dB
ldss	Saturate Drain Current $V_{DS} = 3V, V_{GS} = 0V$	496	620	744	mA
V <sub>DD</sub>	Power Supply Voltage		7	8	V
Rth	Thermal Resistance (Au-Sn Eutectic Attach)		15		°C/W
Tb	Operating Base Plate Temperature	- 35		+ 85	°C

## ABSOLUTE MAXIMUM RATINGS FOR CONTINUOUS OPERATION<sup>1,2</sup>

SYMBOL	CHARACTERISTIC	VALUE	
V <sub>DS</sub>	Drain to Source Voltage	8 V	
$V_{GS}$	Gate to Source Voltage	- 4 V	
I <sub>DD</sub>	Drain Current	ldss	
I <sub>GSF</sub>	Forward Gate Current	9 mA	
P <sub>IN</sub>	Input Power	@ 3dB compression	
Т <sub>СН</sub>	Channel Temperature	150°C	
T <sub>STG</sub>	Storage Temperature	-65/150°C	
Ρ <sub>T</sub>	Total Power Dissipation	7.6W	

1. Operating the device beyond any of the above rating may result in permanent damage. 2. Bias conditions must also satisfy the following equation  $V_{DS}^*I_{DS} < (T_{CH} - T_{HS})/R_{TH}$ ; where  $T_{HS}$  = ambient temperature

Specifications are subject to change without notice.

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